Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating supply voltage		-0.3	625	
Vs	High side floating supply offset voltage		V _B - 25	V _B + 0.3	
V _{HO}	High side floating output voltage		V _S - 0.3	V _B + 0.3	v
V _{LO}	Low side output voltage		-0.3	V _{CC} + 0.3	V
V _{RT}	R _T pin voltage		-0.3	V _{CC} + 0.3	
V _{CT}	C _T pin voltage		-0.3	V _{CC} + 0.3	
Icc	Supply current (note 1)		_	25	mA
I _{RT}	R _T pin current	R _T pin current		5	111/
dV _S /dt	Allowable offset voltage slew rate	Allowable offset voltage slew rate		50	V/ns
PD	Maximum power dissipation @ T _A ≤ +25°C	(8 Lead DIP)	_	1.0	W
		(8 Lead SOIC)	_	0.625	, vv
Rth _{JA}	Thermal resistance, junction to ambient (8 Lead DIP)		_	125	°C/W
	(8 Lead SOIC)		_	200	- C/VV
TJ	Junction temperature		-55	150	
T _S	Storage temperature		-55	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions.

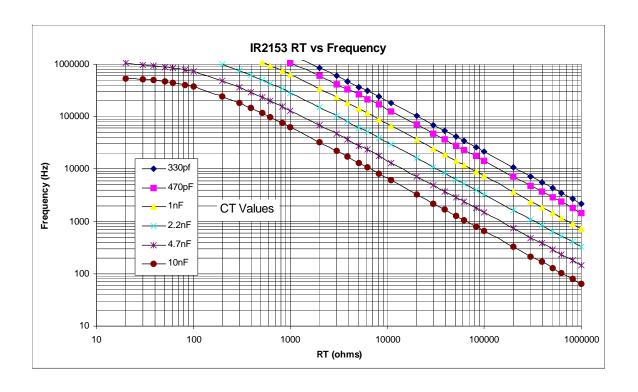
Symbol	Definition	Min.	Max.	Units
V _{Bs}	High side floating supply voltage	V _{CC} - 0.7	VCLAMP	
Vs	Steady state high side floating supply offset voltage	-3.0 (note 2)	600	V
Vcc	Supply voltage	10	VCLAMP	
lcc	Supply current	(note 3)	5	mA
TJ	Junction temperature	-40	125	°C

- Note 1: This IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Please note that this supply pin should not be driven by a DC, low impedance power source greater than the V_{CLAMP} specified in the Electrical Characteristics section.
- Note 2: Care should be taken to avoid output switching conditions where the V_S node flies inductively below ground by more than 5V
- Note 3: Enough current should be supplied to the V_{CC} pin of the IC to keep the internal 15.6V zener diode clamping the voltage at this pin.



Recommended Component Values

Symbol	Component	Min.	Max.	Units
R _T	Timing resistor value	10	_	kΩ
C _T	C _T pin capacitor value	330	_	pF



Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 12V, C_L = 1000 pF, C_T = 1 nF and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Low Voltage Supply Characteristics							
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions	
V _{CCUV+}	Rising V _{CC} undervoltage lockout threshold	8.1	9.0	9.9			
V _{CCUV} -	Falling V _{CC} undervoltage lockout threshold	7.2	8.0	8.8	V		
VCCUVH	V _{CC} undervoltage lockout Hysteresis	0.5	1.0	1.5	1		
I _{QCCUV} Micropower startup V _{CC} supply current		_	75	150	μА	V _{CC} ≤V _{CCUV} -	
IQCC	Quiescent V _{CC} supply current	_	500	950	μΛ		
VCLAMP	V _{CC} zener clamp voltage	14.4	15.6	16.8	V	I _{CC} = 5mA	

Floating Supply Characteristics

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
I _{QBSUV}	Micropower startup V _{BS} supply current	_	0	10		Vcc≤Vccuv-
I _{QBS}	Quiescent VBS supply current	_	30	50	μΑ	
V _{BSMIN}	Minimum required V _{BS} voltage for proper	_	4.0	5.0	V	$V_{CC}=V_{CCUV+} + 0.1V$
	functionality from R _T to HO					
I _{LK}	Offset supply leakage current	_	_	50	μΑ	$V_{B} = V_{S} = 600V$
VF	Bootstrap diode forward voltage (IR2153D)	0.5	_	1.2	V	IF = 250mA

Oscillator I/O Characteristics

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
fosc	Oscillator frequency	19.4	20	20.6	kHz	$R_T = 36.9k\Omega$
		94	100	106	KHZ	$RT = 7.43k\Omega$
d	RT pin duty cycle	48	50	52	%	fo < 100kHz
I _{CT}	C _T pin current	_	0.001	1.0	uA	
ICTUV	UV-mode C _T pin pulldown current	0.30	0.70	1.2	mA	V _{CC} = 7V
VcT+	Upper C _T ramp voltage threshold	_	8.0	_		
Vcт-	Lower C _T ramp voltage threshold	_	4.0	_	V	
VCTSD	CT voltage shutdown threshold	1.8	2.1	2.4	Ī	
V _{RT+}	High-level RT output voltage, VCC - VRT	_	10	50		I _{RT} = 100μA
		_	100	300		I _{RT} = 1mA
VRT-	Low-level R _T output voltage	_	10	50	1	I _{RT} = 100μA
		_	100	300	mV	I _{RT} = 1mA
VRTUV	UV-mode R _T output voltage	_	0	100	1111	V _{CC} ≤V _{CCUV} -
VRTSD	SD-Mode RT output voltage, VCC - VRT	_	10	50	1	$I_{RT} = 100 \mu A$,
						$V_{CT} = 0V$
		_	10	300	1	$I_{RT} = 1mA$,
						V _{CT} = 0V

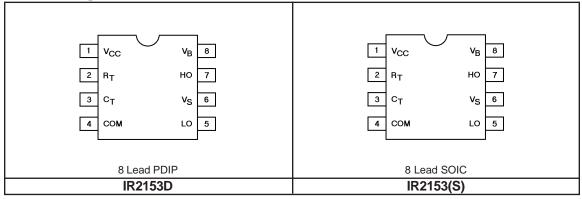
Electrical Characteristics (cont.)

Gate Driver Output Characteristics							
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions	
VoH	High level output voltage, V _{BIAS} -V _O	_	0	100		I _O = OA	
VOL	Low-level output voltage, VO	_	0	100	mV	I _O = OA	
VOL_UV	UV-mode output voltage, VO	_	0	100	11111	I _O = OA	
						$I_O = OA$ $V_{CC} \le V_{CCUV}$	
tr	Output rise time	_	80	150			
tf	Output fall time	_	45	100	nsec		
t _{sd}	Shutdown propogation delay	_	660	_	1		
td	Output deadtime (HO or LO)	0.75	1.20	1.65	μѕес		

Lead Definitions

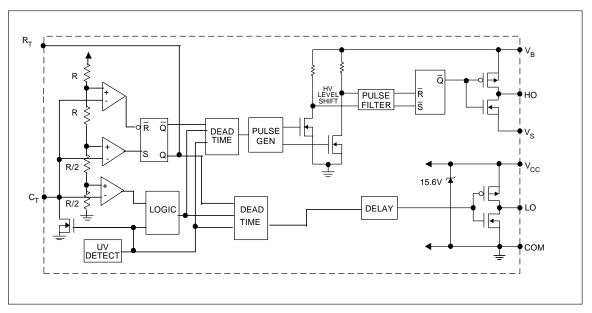
Symbol	Description
Vcc	Logic and internal gate drive supply voltage
R _T	Oscillator timing resistor input
C _T	Oscillator timing capacitor input
COM	IC power and signal ground
LO	Low side gate driver output
VS	High voltage floating supply return
НО	High side gate driver output
V _B	High side gate driver floating supply

Lead Assignments

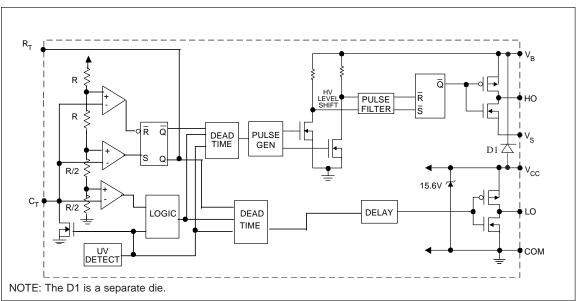


NOTE: The IR2153D is offered in 8 lead PDIP only.

Functional Block Diagram for IR2153(S)

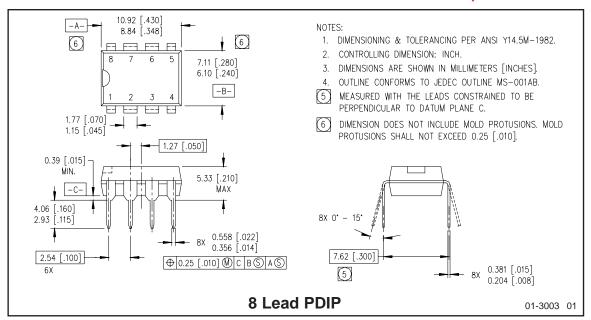


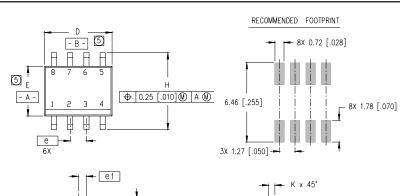
Functional Block Diagram for IR2153D



IR2153(D)(S) & (PbF)

NOTE: For new designs, we recommend IR's new product IRS2153D





0.10 [.004]

DIM	INCH	IES	MILLIME	TERS
DIM	MIN	MAX	MIN	MAX
Α	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
В	.014	.018	0.36	0.46
С	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
Ε	.150	.157	3.81	3.99
е	.050 B	ASIC	1.27 BASIC	
e 1	.025 B	ASIC	0.635	BASIC
Н	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	.016	.050	0.41	1.27
У	0.	8.	0.	8,



- C -

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.

→ | 0.25 [.010] M | C | A S | B S |

- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.

 MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.006].
- (6) DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

8 Lead SOIC

6

01-0021 08

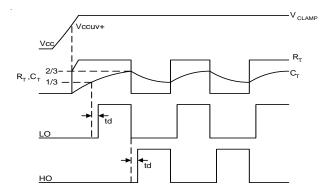


Figure 1. Input/Output Timing Diagram

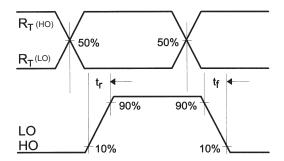


Figure 2. Switching Time Waveform Definitions

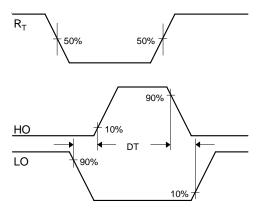
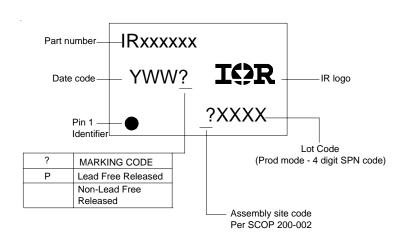


Figure 3. Deadtime Waveform Definitions

LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)

8-Lead PDIP IR2153 order IR2153 8-Lead SOIC IR2153S order IR2153S 8-Lead PDIP IR2153D order IR2153D

Leadfree Part

8-Lead PDIP IR2153 order IR2153PbF 8-Lead SOIC IR2153S order IR2153SPbF 8-Lead PDIP IR2153D order IR2153DPbF



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

This product has been qualified per industrial level

Data and specifications subject to change without notice. 5/21/2020